

PRODUCT SPECIFICATION

PTI-0914
Photodiode Sensor, Round, 900nm

REV: -101

2010-MAR-14

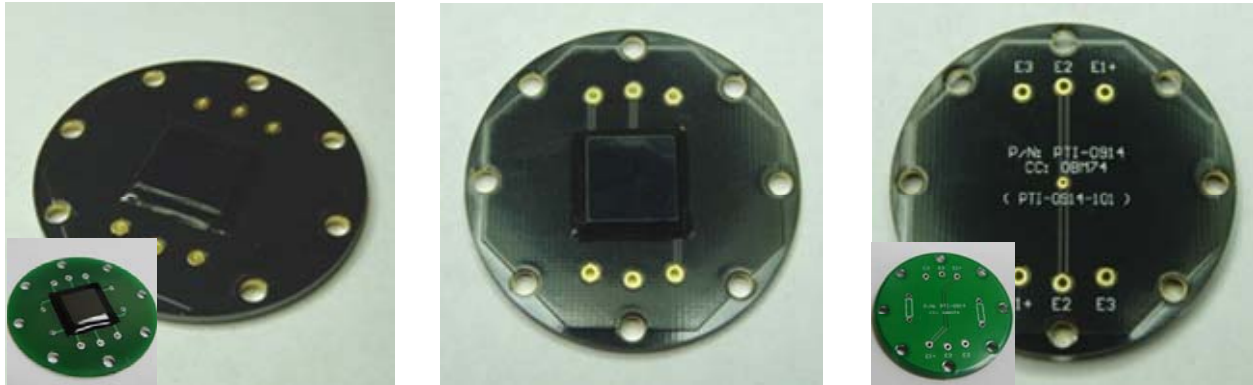
TYPE: Photodiode - PIN

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Specifications

- Si Photodiode with active area of 9.4mm X 9.4mm (Chip Size: 10mm X 10mm)
- E1: Anode (P side), E2: Cathode (N side), E3: Shield (isolated)
- Wavelength: 900nm \pm 20nm
- Total Capacitance (CT): 700pf
- Short Circuit Current (ISC): 750uA
- Reverse Breakdown Voltage: 10v
- Open Circuit Voltage (VOC): 450mV
- Temperature Range: Operating -20°C to +60°C, Storage -33°C to +70°C

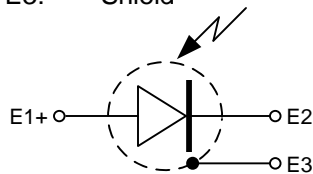
Pictures



Note: Board can be ordered in different colors: Blk, Grn or Red.

Pin Connections & Housing Dimensions

E1+: Anode
E2: Cathode
E3: Shield



Overall Dia: 1.625" (41.2mm)
(Tolerances: \pm .005")

